

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	
Filing Date	June 28, 2003
First Named Inventor	Chih-Hsin Wang
Art Unit	
Examiner Name	
Attorney Docket Number	

Sheet 1 of 1

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
MH		US- 5,780,341	07-14-1998	Seiki Ogura	Figs. 4A, 4B, 6A, 6B
		US-			Fig. 7A
MH		US- 4,957,877	09-18-1990	Simon M. Tam et al.	Figs. 5A, 5B
MH		US- 5,146,426	09-08-1992	Mukherjee, et al.	p2, c5 L17-20
		US-			c3 L46-48, c6 L45-53
MH		US- 5,432,739	07-11-1995	H. B. Pein	c3 L57-65
		US-			
MH		US- 5,115,289	05-19-1992	Hisamoto et al.	Figs. 1, 3b
		US-			c10 L66-68, c11 L44
		US-			c13 L27, c17 L14-68
MH		US- 6,479,863 B2	11-12-2002	John Caywood	Figs. 3b, 5b, 17d,
		US-			17e, 18d
MH		US- 6,372,617 B1	04-16-2002	T. Kitamura	Fig. 3A
		US-			
		US-			
		US-			
		US-			
		US-			
		US-			

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T ⁶

Examiner
Signature*M. H. Hsin*Date
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04/23/04

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of 1

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
USA		Kitamura et al., "A Low Voltage Operating Flash Cell with High Coupling Ratio Using Horned Floating Gate with Fine HSG," Symposium on VLSI Technology, p. 104, 1998	
USA		Lai, "Flash Memories: Where We Were and Where We Are Going", IEDM Technical Digest, pp. 971-973, 1998.	
USA		Kuo et al., "TEFET - A High Density, Low Erase Voltage, Trench Flash EEPROM", Symposium on VLSI Technology, p. 51, 1994	
USA		Wang et al., "Three-Dimensional DIBL for Shallow-Trench Isolated MOSFET's", IEEE Trans. on Electron Devices, vol. 46, pp. 139-144, 1999	

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